Product data sheet

# 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- Enhanced power dissipation capability: Ptot = 980 mW
- ElectroStatic Discharge (ESD) protection 2 kV HBM
- AEC-Q101 qualified

## 3. Applications

- LED driver
- Power management
- High-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

| Symbol            | Parameter                        | Conditions  |     | Min | Тур | Max  | Unit |
|-------------------|----------------------------------|---|-----|-----|-----|------|------|
| $V_{DS}$          | drain-source voltage             | T <sub>j</sub> = 25 °C                                      |     | -   | -   | -20  | V    |
| V <sub>GS</sub>   | gate-source voltage              |   |     | -8  | -   | 8    | V    |
| I <sub>D</sub>    | drain current                    | V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s | [1] | -   | -   | -5.6 | Α    |
| Static characte   | eristics                         |   |     |     |     |      | ,    |
| R <sub>DSon</sub> | drain-source on-state resistance | $V_{GS}$ = -4.5 V; $I_D$ = -4.5 A; $T_j$ = 25 °C            |     | -   | 27  | 32   | mΩ   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



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# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline      | Graphic symbol  |
|-----|--------|-------------|-------------------------|-----------------|
| 1   | G      | gate        | 3                       | D<br>I          |
| 2   | S      | source      |                         |                 |
| 3   | D      | drain       | 1 2<br>TO-236AB (SOT23) | G S S 017aaa259 |

# 6. Ordering information

Table 3. Ordering information

| Type number | Package  |  |         |  |  |  |
|-------------|----------|--|---------|--|--|--|
|             | Name     | Description                              | Version |  |  |  |
| PMV27UPEA   | TO-236AB | plastic surface-mounted package; 3 leads | SOT23   |  |  |  |

# 7. Marking

Table 4. Marking codes

| Type number | Marking code [1] |
|-------------|------------------|
| PMV27UPEA   | AE%              |

[1] % = placeholder for manufacturing site code

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol               | Parameter                                | Conditions  |     | Min | Max  | Unit |
|----------------------|--|---|-----|-----|------|------|
| $V_{DS}$             | drain-source voltage                     | T <sub>j</sub> = 25 °C  |     | -   | -20  | V    |
| $V_{GS}$             | gate-source voltage                      |   |     | -8  | 8    | V    |
| I <sub>D</sub>       | drain current                            | $V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$ | [1] | -   | -5.6 | Α    |
|                      |  | V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C                    | [1] | -   | -4.5 | Α    |
|                      |  | V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C                   | [1] | -   | -2.8 | Α    |
| I <sub>DM</sub>      | peak drain current                       | $T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$                   |     | -   | -18  | Α    |
| E <sub>DS(AL)R</sub> | repetitive drain-source avalanche energy | $I_D$ = -1.8 A; $T_{j(init)}$ = 25 °C; DUT in avalanche (unclamped).  |     | -   | 19   | mJ   |
| P <sub>tot</sub>     | total power dissipation                  | T <sub>amb</sub> = 25 °C  | [2] | -   | 490  | mW   |
|                      |  |   | [1] | -   | 980  | mW   |
|                      |  | T <sub>sp</sub> = 25 °C   |     | -   | 4150 | mW   |
| T <sub>j</sub>       | junction temperature                     |   |     | -55 | 150  | °C   |
| T <sub>amb</sub>     | ambient temperature                      |   |     | -55 | 150  | °C   |
| T <sub>stg</sub>     | storage temperature                      |   |     | -65 | 150  | °C   |
| Source-drain         | diode                                    |   |     |     |      |      |
| Is                   | source current                           | T <sub>amb</sub> = 25 °C  | [1] | -   | -1.2 | Α    |
| ESD maximu           | m rating                                 |   | •   |     |      | -    |
| V <sub>ESD</sub>     | electrostatic discharge voltage          | НВМ   | [3] | -   | 2000 | V    |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Measured between all pins.

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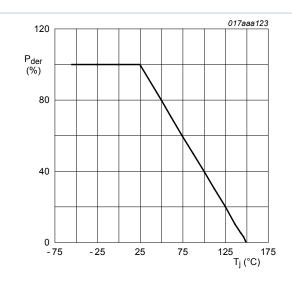


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

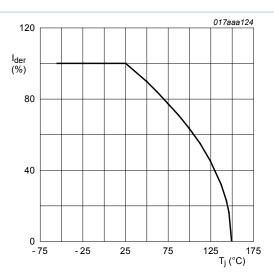


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

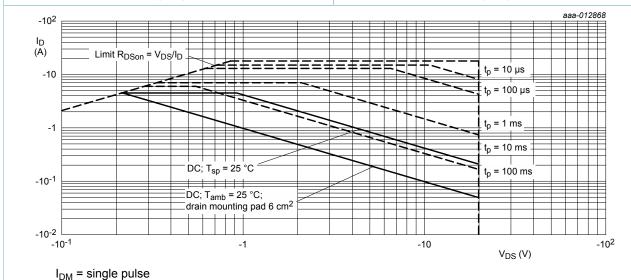


Fig. 3. Safe operating area: junction to ambient: continuous and pea

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol               | Parameter                | Conditions           |     | Min | Тур | Max | Unit |
|----------------------|--------------------------|----------------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub> | thermal resistance       | in free air          | [1] | -   | 222 | 255 | K/W  |
|                      | from junction to ambient |                      | [2] | -   | 111 | 128 | K/W  |
|                      |                          | in free air; t ≤ 5 s | [2] | -   | 74  | 85  | K/W  |

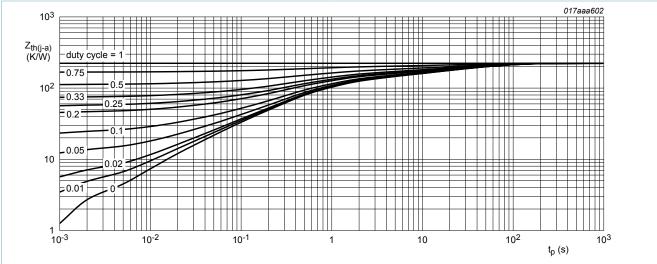
PMV27UPEA

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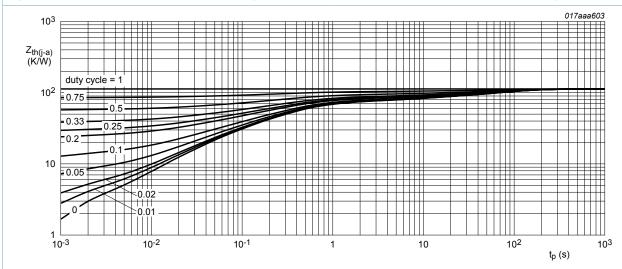
| Symbol                | Parameter  | Conditions | Min | Тур | Max | Unit |
|-----------------------|--|------------|-----|-----|-----|------|
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point |            | -   | 25  | 30  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm<sup>2</sup>

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, P-channel Trench MOSFET

# 10. Characteristics

Table 7. Characteristics

| Symbol   | Parameter                         | Conditions   | Min   | Тур  | Max   | Unit |
|--|-----------------------------------|--|-------|------|-------|------|
| Static chara                                       | acteristics                       |  |       |      |       |      |
| $V_{(BR)DSS}$                                      | drain-source<br>breakdown voltage | $I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$                              | -20   | -    | -     | V    |
| $V_{GSth}$   | gate-source threshold voltage     | $I_D$ = -250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C                  | -0.45 | -0.7 | -0.95 | V    |
| I <sub>DSS</sub>                                   | drain leakage current             | $V_{DS}$ = -20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C                            | -     | -    | -1    | μA   |
| I <sub>GSS</sub>                                   | gate leakage current              | V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C       | -     | -    | 10    | ##A  |
|  |                                   | V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C      | -     | -    | -10   | μA   |
|  |                                   | $V_{GS}$ = 4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                            | -     | -    | 5     | μA   |
|  |                                   | $V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C                           | -     | -    | -5    | μA   |
| R <sub>DSon</sub> drain-source on-state resistance | drain-source on-state             | $V_{GS} = -4.5 \text{ V}; I_D = -4.5 \text{ A}; T_j = 25 \text{ °C}$       | -     | 27   | 32    | mΩ   |
|  | resistance                        | V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -4.5 A; T <sub>j</sub> = 150 °C | -     | 40   | 48    | mΩ   |
|  |                                   | $V_{GS}$ = -2.5 V; $I_D$ = -3.8 A; $T_j$ = 25 °C                           | -     | 38   | 45    | mΩ   |
|  |                                   | $V_{GS}$ = -1.8 V; $I_D$ = -3 A; $T_j$ = 25 °C                             | -     | 50   | 63    | mΩ   |
| g <sub>fs</sub>                                    | forward transconductance          | $V_{DS}$ = -10 V; $I_{D}$ = -2 A; $T_{j}$ = 25 °C                          | -     | 15   | -     | S    |
| R <sub>G</sub>                                     | gate resistance                   | f = 1 MHz  | -     | 10.7 | -     | Ω    |
| Dynamic ch   | naracteristics                    |  |       |      |       |      |
| Q <sub>G(tot)</sub>                                | total gate charge                 | $V_{DS}$ = -10 V; $I_{D}$ = -4.4 A; $V_{GS}$ = -4.5 V;                     | -     | 14.7 | 22.1  | nC   |
| $Q_{GS}$   | gate-source charge                | T <sub>j</sub> = 25 °C   | -     | 2.6  | -     | nC   |
| $Q_{GD}$   | gate-drain charge                 |  | -     | 2.5  | -     | nC   |
| C <sub>iss</sub>                                   | input capacitance                 | $V_{DS}$ = -10 V; f = 1 MHz; $V_{GS}$ = 0 V;                               | -     | 1820 | -     | pF   |
| C <sub>oss</sub>                                   | output capacitance                | T <sub>j</sub> = 25 °C   | -     | 208  | -     | pF   |
| C <sub>rss</sub>                                   | reverse transfer capacitance      |  | -     | 146  | -     | pF   |
| t <sub>d(on)</sub>                                 | turn-on delay time                | $V_{DS}$ = -10 V; $I_{D}$ = -4.4 A; $V_{GS}$ = -4.5 V;                     | -     | 11   | -     | ns   |
| t <sub>r</sub>                                     | rise time                         | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$                                       | -     | 30   | -     | ns   |
| t <sub>d(off)</sub>                                | turn-off delay time               |  | -     | 83   | -     | ns   |
| t <sub>f</sub>                                     | fall time                         |  | -     | 39   | -     | ns   |
| Source-dra   | in diode                          |  | I     | 1    | 1     | 1    |
| V <sub>SD</sub>                                    | source-drain voltage              | $I_S = -1.2 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$    | -     | -0.7 | -1.2  | V    |
|  |                                   |  |       |      |       |      |

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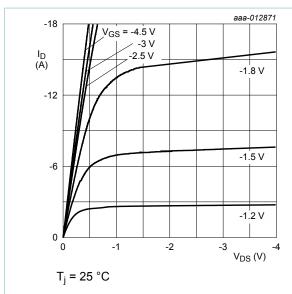


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

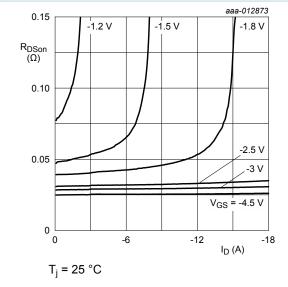


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

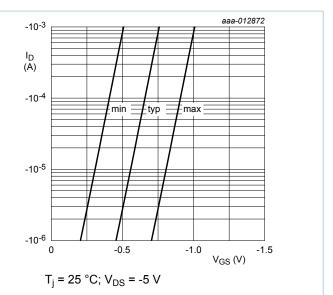


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

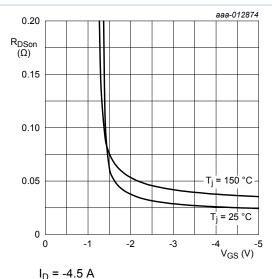


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

### 20 V, P-channel Trench MOSFET

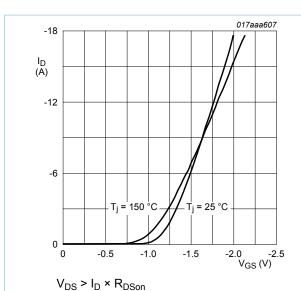


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

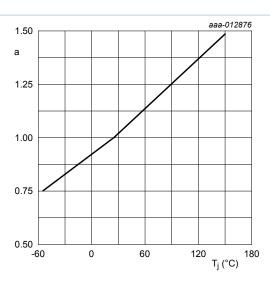


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

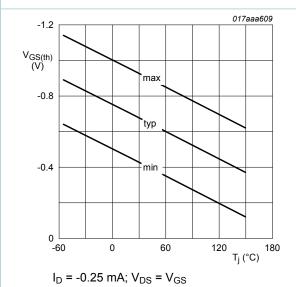


Fig. 12. Gate-source threshold voltage as a function of junction temperature

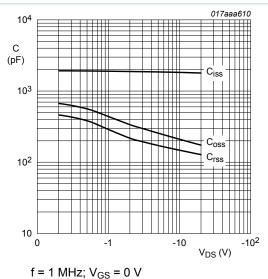


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### 20 V, P-channel Trench MOSFET

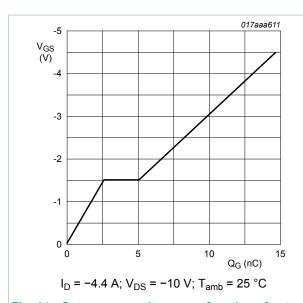


Fig. 14. Gate-source voltage as a function of gate charge; typical values

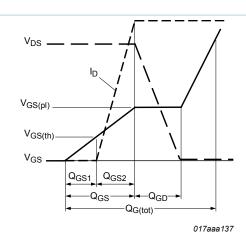


Fig. 15. MOSFET transistor: Gate charge waveform definitions

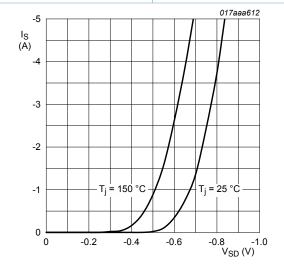
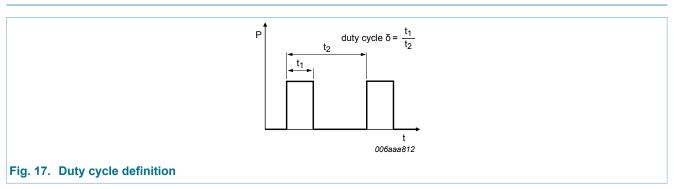


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

 $V_{GS} = 0 V$ 



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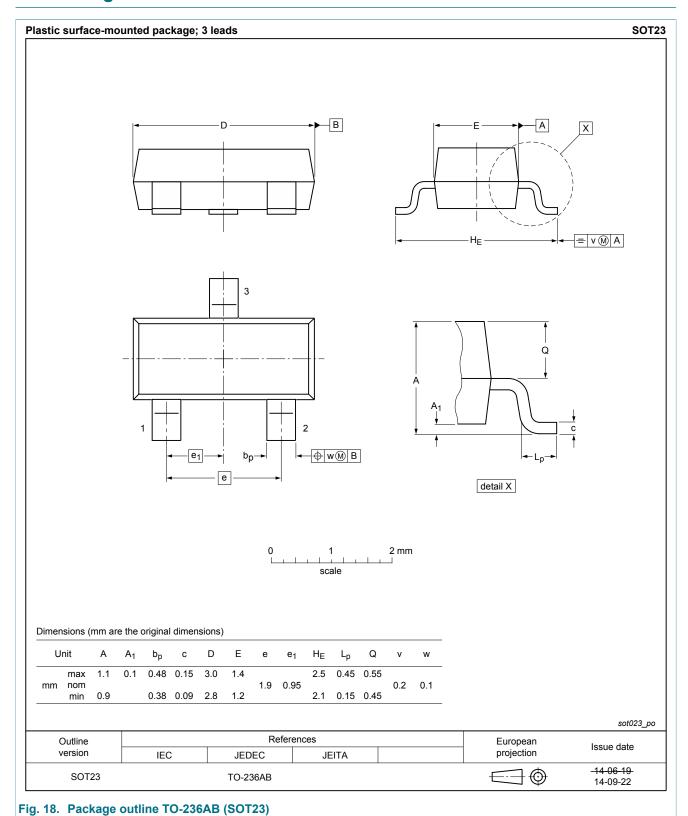
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# 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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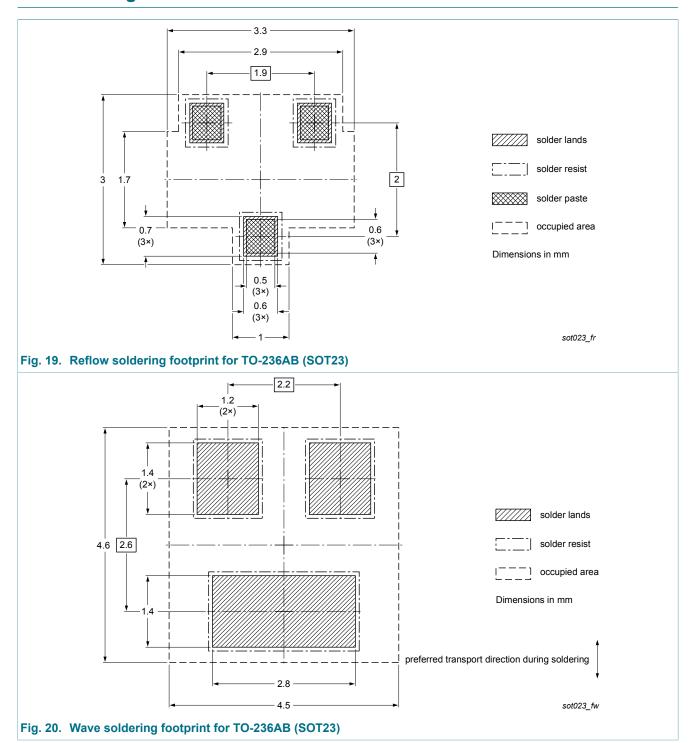
# 12. Package outline



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# 13. Soldering



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# 14. Revision history

### Table 8. Revision history

| Data sheet ID | Release date | Data sheet status  | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PMV27UPEA v.1 | 20151030     | Product data sheet | -             | -          |

#### 20 V, P-channel Trench MOSFET

## 15. Legal information

#### 15.1 Data sheet status

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary<br>[short] data<br>sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product<br>[short] data<br>sheet     | Production         | This document contains the product specification.                                     |

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